L	Hits	Search Text	DB	Time stamp
Number				
2	2	<pre>@ad<=20000203 and 'n' adj1 'electrode' with 'ITO'</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/06/01 09:57
3	6	<pre>@ad<=20000203 and 'LED'and 'n electrode' with 'ITO'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/01
		WICH IIO	EPO; JPO; DERWENT; IBM TDB	00.13
4	1	<pre>@ad<=20000203 and 'LED' and 'n electrode' with 'ITO'</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/06/01 08:13
5	2	@ad<=20000203 and 'n electrode' with	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/01 08:17
6	2	@ad<=20000203 and 'ITO' with	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/01
	2	'n-electrode'	US-PGPUB; EPO; JPO; DERWENT;	08:17
7	9	<pre>@ad<=20000203 and 'transparent' with 'n-electrode'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/01 08:18
188	3	<pre>@ad<=20000203 and 'gallium compound' and 'n electrode' and 'p electrode'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/01
189	1207	@ad<=20000203 and (257/98).ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/01
			US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12:23
190	661	@ad<=20000203 and (257/94).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/01 08:38
191	444	@ad<=20000203 and (257/96).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/01 08:38
192	326	@ad<=20000203 and (257/97).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/01
193	936	@ad<=20000203 and (257/103).ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/01
	, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		US-PGPUB; EPO; JPO; DERWENT;	08:39
194	326	@ad<=20000203 and (257/13).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/01 08:40
195	235	@ad<=20000203 and (257/15).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/01 08:40
			DERWENT; IBM TDB	

Search History 6/1/04 12:27:14 PM Page 1

196	341	@ad<=20000203 and (257/22).ccls.	TICDAM.	2004/06/01
196	241	ead(-20000203 and (237/22).CCIS.	USPAT; US-PGPUB;	08:40
			EPO; JPO;	
			DERWENT;	
198	3	 @ad<=20000203 and 'n-electrode' same	<pre>IBM_TDB USPAT;</pre>	2004/06/01
190]	'ITO'	US-PGPUB;	10:00
			EPO; JPO;	
			DERWENT;	
	4.50		IBM_TDB	0004/06/04
200	152	<pre>@ad<=20000203 and 'LED' same 'ITO' with 'electrode'</pre>	USPAT; US-PGPUB;	2004/06/01
		electiode	EPO; JPO;	10.11
			DERWENT;	
			IBM_TDB	
202	4	@ad<=20000203 and 'gallium nitride' same	USPAT;	2004/06/01
		'ITO' with 'electrode'	US-PGPUB; EPO; JPO;	10:02
			DERWENT;	
	1		IBM_TDB	
203	. 48	@ad<=20000203 and 'LED' with 'ITO' with	USPAT;	2004/06/01
		'electrode'	US-PGPUB; EPO; JPO;	10:16
			DERWENT;	
			IBM TDB	
204	1		USPĀT;	2004/06/01
		with 'ITO' with 'electrode'	US-PGPUB;	10:16
			EPO; JPO; DERWENT;	
			IBM TDB	
205	49	@ad<=20000203 and 'nitride semiconductor'	USPĀT;	2004/06/01
		and 'ITO' with 'electrode'	US-PGPUB;	10:38
			EPO; JPO;	
			DERWENT; IBM TDB	
206	47	@ad<=20000203 and 'n' near2 'electrode'	USPAT;	2004/06/01
		with 'ITO'	US-PGPUB;	10:38
			EPO; JPO;	
			DERWENT; IBM TDB	
207	13	@ad<=20000203 and 'n' near1 'electrode'	USPAT;	2004/06/01
		with 'ITO'	US-PGPUB;	10:38
			EPO; JPO;	
			DERWENT; IBM TDB	
208	1323	@ad<=20000203 and (257/99).ccls.	USPAT;	2004/06/01
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	12:24
			EPO; JPO;	
			DERWENT; IBM TDB	
_	507	(257/21).CCLS.	USPAT;	2004/05/30
		· · · ·	US-PGPUB;	09:18
			EPO; JPO;	
			DERWENT; IBM TDB	
_	16	((257/21).CCLS.) and @ad<=20000203 and	USPAT;	2002/11/01
	1	'Gan'	US-PGPUB;	10:53
	1		EPO; JPO;	
			DERWENT; IBM TDB	
_	107	@ad<=20000203 and 'GaN' and 'n-type	USPAT;	2004/05/28
		electrode' and 'p-type electrode'	US-PGPUB;	13:32
			EPO; JPO;	
	1		DERWENT;	
_	1	 @ad<=20000203 and 'GaN' and 'n-type	IBM_TDB USPAT;	2004/05/29
	1	electrode' and 'p-type electrode' with	US-PGPUB;	07:36
		'pad'	EPO; JPO;	
			DERWENT;	
	L		IBM_TDB_	l

_	2	("6172382").PN.	USPAT; US-PGPUB; EPO; JPO;	2002/11/01
			DERWENT; IBM TDB	
-	16	((257/21).CCLS.) and @ad<=20000203 and	USPĀT;	2002/04/22
		'Gan'	US-PGPUB; EPO; JPO;	16:46
			DERWENT;	
_	273	 @ad<=20000203 and 'GaN' and 'electrode'	IBM_TDB USPAT;	2002/04/23
		with 'transparent'	US-PGPUB; EPO; JPO;	11:26
			DERWENT;	
_	3	 @ad<=20000203 and 'GaN' and 'n-type	IBM_TDB USPAT;	2002/04/23
		electrode' and 'p-type electrode' with	US-PGPUB;	09:56
		'transparent'	EPO; JPO; DERWENT;	
_	0	 @ad<=20000203 and 'GaN' and 'n-type	IBM_TDB USPAT;	2002/04/23
		electrode' with 'trans'	US-PGPUB;	11:01
			EPO; JPO; DERWENT;	
	2	0nd <- 20000202 and 15 N1 and 15 time	IBM_TDB USPAT;	2002/04/23
_	4	<pre>@ad<=20000203 and 'GaN' and 'n-type electrode' with 'transmissive'</pre>	US-PGPUB;	11:01
			EPO; JPO; DERWENT;	
			IBM_TDB	0000/11/01
_	7	<pre>@ad<=20000203 and 'GaN' and 'transmissive electrode'</pre>	USPAT; US-PGPUB;	2002/11/01 16:06
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	996	(257/59).CCLS.	USPAT; US-PGPUB;	2002/11/01
			EPO; JPO; DERWENT;	
		,	IBM_TDB	
_	0	("103 and 'GaN'").PN.	USPAT; US-PGPUB;	2002/04/23
			EPO; JPO; DERWENT;	
	_		IBM TDB	
-	6	((257/59).CCLS.) and 'GaN'	USPAT; US-PGPUB;	2002/04/23 11:23
			EPO; JPO; DERWENT;	
		(72)	IBM_TDB	
_	837	(257/72).CCLS.	USPAT; US-PGPUB;	2002/11/01 10:53
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	((257/72).CCLS.) and 'GaN' and 'transparent electrode'	USPAT; US-PGPUB;	2002/04/23 11:24
		_	EPO; JPO; DERWENT;	
			IBM_TDB	
-	166	<pre>@ad<=20000203 and 'GaN' and 'transparent electrode'</pre>	USPAT; US-PGPUB;	2002/04/23 11:27
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	115	<pre>@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode'</pre>	USPAT; US-PGPUB;	2003/11/06 15:11
		2 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	EPO; JPO;	
			DERWENT; IBM_TDB	

		1 () 5 7 () 1	C	
_	16	((257/21).CCLS.) and @ad<=20000203 and	USPAT;	2002/11/01
		'GaN'	US-PGPUB;	10:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1128	(257/59).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	10:54
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	957	(257/72).CCLS.	USPAT;	2002/11/01
		(207,72,70020.	US-PGPUB;	10:54
			EPO; JPO;	10.01
			DERWENT;	:
			IBM TDB	}
1_	560	(438/22).CCLS.	USPAT;	2002/11/01
] 360	(430/22).0013.	,	
			US-PGPUB;	11:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1108	((438/22) or (257/79)).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	11:07
			EPO; JPO;	
1			DERWENT;	1
1			IBM TDB	1
-	106	@ad<=20000203 and 'GaN' and 'n-type' and	USPAT;	2002/11/01
		'p-type' and 'ITO'	US-PGPUB;	12:03
1		* **	EPO; JPO;	
1			DERWENT;	
1			IBM TDB	
_	35	@ad<=20000203 and 'GaN' and 'n-type' same	USPAT;	2002/11/01
	33	'ITO'	US-PGPUB;	13:48
		110		12:40
]		EPO; JPO;	
			DERWENT;	
		//055/40 45	IBM_TDB	0000 (11 (01
-	7979	((257/13-15) or (257/79-103)).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	13:48
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	463	(((257/13-15) or (257/79-103)).CCLS.) and	USPAT;	2003/06/04
		@ad<=20000203 and 'GaN'	US-PGPUB;	10:03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	709	(438/22-24).CCLS.	USPĀT;	2002/11/01
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	@ad<=20000203 and 'light emitting diode'	USPAT;	2002/11/01
l		and 'n-type electrode' with 'ITO'	US-PGPUB;	15:58
		and it type creetiods with ito	EPO; JPO;	
			DERWENT;	
1			IBM TDB	
1	244	0-4<-20000202 -m4 114-4-+		2002/11/01
-	244	@ad<=20000203 and 'light emitting diode'	USPAT;	2002/11/01
		and 'n-type electrode'	US-PGPUB;	15:47
1			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	0000/11/01
-	13	(@ad<=20000203 and 'light emitting diode'	USPAT;	2002/11/01
		and 'n-type electrode') and ITO	US-PGPUB;	15:48
-			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	@ad<=20000203 and 'n-type electrode' with	USPAT;	2002/11/01
		'ITO'	US-PGPUB;	15:58
1			EPO; JPO;	
			DERWENT;	
1			IBM TDB	

-	0	@ad<=20000203 and 'n-type electrode' near	USPAT;	2002/11/01
		'ITO'	US-PGPUB;	15:59
			EPO; JPO;	
			DERWENT; IBM TDB	
_	55	@ad<=20000203 and 'n-type electrode' and	USPAT;	2002/11/01
	33	'ITO'	US-PGPUB;	16:03
		110	EPO; JPO;	10.05
			DERWENT;	
			IBM TDB	
-	1	<pre>@ad<=20000203 and 'n-type electrode' and</pre>	USPAT;	2002/11/01
]	'TCO'	US-PGPUB;	16:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/11/01
_	49		USPAT;	2002/11/01 16:06
		electrode'	US-PGPUB; EPO; JPO;	16:06
			DERWENT;	
			IBM TDB	
_	8	@ad<=20000203 and 'GaN' and 'transmissive	USPAT;	2002/11/01
		electrode'	US-PGPUB;	16:07
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1197	@ad<=20000203 and (257/98).ccls.	USPAT;	2004/06/01
			US-PGPUB;	08:36
			EPO; JPO;	
			DERWENT;	
	145	@ad<=20000203 and (257/91).ccls.	<pre>IBM_TDB USPAT;</pre>	2003/06/03
-	145	@ad<=20000203 and (257/91).CCIS.	US-PGPUB;	09:52
			EPO; JPO;	09.32
]		DERWENT;	
			IBM TDB	
_	655	@ad<=20000203 and (257/94).ccls.	USPAT;	2003/06/03
			US-PGPUB;	09:53
			EPO; JPO;	
			DERWENT;	
		0.1.00000000 1.4057/1031	IBM_TDB	2002/06/02
j -	925	@ad<=20000203 and (257/103).ccls.	USPAT; US-PGPUB;	2003/06/03 09:53
			EPO; JPO;	09.53
			DERWENT;	
			IBM TDB	
_	1315	@ad<=20000203 and (257/99).ccls.	USPAT;	2003/06/03
			US-PGPUB;	09:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/06/00
-	2	("6100545").PN.	USPAT;	2003/06/03
			US-PGPUB;	09:54
			EPO; JPO; DERWENT;	
i			IBM TDB	
_	7	 @ad<=20000203 and 'GaN' with	USPAT;	2003/06/03
	1 '	'transparent' and 'n-type electrode' and	US-PGPUB;	13:56
		'p-type electrode'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	22	@ad<=20000203 and 'GaN' and 'transparent'	USPĀT;	2003/06/03
		and 'n-type electrode' and 'p-type	US-PGPUB;	13:29
		electrode'	EPO; JPO;	
			DERWENT;	
		And - 20000202 and 10aN! and 1+nangnament!	IBM_TDB USPAT;	2003/06/03
-	8	<pre>@ad<=20000203 and 'GaN' and 'transparent' same 'n-type electrode' and 'p-type</pre>	US-PGPUB;	13:39
		electrode'	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	l	<u> </u>		

-	24	<pre>@ad<=20000203 and 'GaN' with 'transparent electrode'</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/06/03 13:40
			DERWENT; IBM_TDB	
_	16	<pre>@ad<=20000203 and 'Gallium nitride' with 'transparent electrode'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/03
-	26	@ad<=20000203 and 'GaN' and 'n-type' with 'p-type' same 'transparent electrode'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/03 13:57
-	0	<pre>@ad<=20000203 and 'GaN' and 'n-type transparent electrode' same 'p-type transparent electrode'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/03 13:58
-	0	<pre>@ad<=20000203 and 'n-type transparent electrode' same 'p-type transparent electrode'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/03 13:59
-	486	((((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:11
-	314	((((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'gallium nitride'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/04 10:04
-	2	"20010042860"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/06 13:01
-	496	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:12
-	112	<pre>@ad<=20000203 and 'GaN' and 'n-type electrode' same 'p-type electrode'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:14
-	46	@ad<=20000203 and 'GaN' and 'n-type electrode' same 'thickness'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:24
-	3	@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:26
-	2	(@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode') and thickness near3 (nm nanometer)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:28
-	25	<pre>@ad<=20000203 and 'GaN' and electrode near3 thickness near3 (nm nanometer)</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 15:39
			IBM TDB	

_	1	@ad<=20000203 and 'GaN' and electrode	USPAT;	2003/11/06
		near3 thickness near3 '30'	US-PGPUB;	15:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	•
ļ -	40	@ad<=20000203 and 'GaN' same 'transparent	USPAT;	2003/11/06
		electrode'	US-PGPUB;	15:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20000203 and 'GaN' same	USPAT;	2003/11/06
		'transparent' with 'n type electrode'	US-PGPUB;	15:36
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
_	116	@ad<=20000203 and 'GaN' and 'n' with	USPAT;	2003/11/06
	110	'electrode' same '50'	US-PGPUB;	15:40
		electione same so	EPO; JPO;	15.40
			DERWENT;	
			IBM TDB	
		0.14 00000000 1 10-11 1 1-1	_	2002/11/06
-	33		USPAT;	2003/11/06
		'electrode' with '50'	US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	• · · · · · · · · · · · · · · · · · ·	USPAT;	2004/05/29
		'electrode' with '50 nm'	US-PGPUB;	07:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	19	@ad<=20000203 and 'GaN' and 'n' with	USPAT;	2003/11/06
		'electrode' with '50 nm'	US-PGPUB;	15:47
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	10	@ad<=20000203 and 'GaN' and 'n' adj2	USPAT;	2003/11/06
		'electrode' with '50 nm'	US-PGPUB;	15:48
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1 -	2	'reflective index' same 'GaN'	USPAT;	2004/03/05
	_		US-PGPUB;	13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	_ n	'reflective index of GaN'	USPAT;	2004/03/05
		Lorro Lincon or our	US-PGPUB;	13:08
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	380	'refractive index' same 'GaN'	USPAT;	2004/05/29
		TOTTACOTIVE THUCK Same Gan	US-PGPUB;	06:01
			EPO; JPO;	~~~~
			DERWENT;	
	[IBM TDB	
	0	 'refractive index of GaN'	USPAT;	2004/03/05
-	1	Tellactive fudex of Gan.	USPAT; US-PGPUB;	13:10
}				12.10
			EPO; JPO;	
			DERWENT;	
		10.371	IBM_TDB	2004/03/05
-	199	'GaN' with 'refractive index'	USPAT;	2004/03/05
1			US-PGPUB;	13:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/05
-	283	@ad<=20000103 and 'sapphire' with	USPAT;	2004/03/05
		'refractive index'	US-PGPUB;	13:25
			EPO; JPO;	
			DERWENT;	<u> </u>
			IBM TDB	

	6040	@ad<=20000103 and 'air' with 'refractive	IISDAT.	2004/02/05
1	6040	ead<=20000103 and 'air' with 'refractive index'	USPAT; US-PGPUB;	2004/03/05 13:29
		Index	EPO; JPO;	13.23
ļ			DERWENT;	
İ			IBM_TDB	
[-	103	@ad<=20000203 and 'GaN' with 'substrate'	USPAT;	2004/05/28
		and 'n-type electrode' and 'p-type	US-PGPUB;	15:57
İ		electrode'	EPO; JPO; DERWENT;	
			IBM TDB	
_	18	@ad<=20000203 and 'GaN' adj1 'substrate'	USPAT;	2004/05/28
		and 'n-type electrode' and 'p-type	US-PGPUB;	13:54
		electrode'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	82	@ad<=20000203 and 'GaN' same 'sapphire'	USPAT;	2004/05/28
		same 'substrate' and 'n-type electrode' and 'p-type electrode'	US-PGPUB; EPO; JPO;	15:57
		and p-type electione	DERWENT;	
			IBM TDB	
-	78	@ad<=20000203 and 'substrate' same 'GaN'	USPAT;	2004/05/28
		with 'sapphire' and 'n-type electrode'	US-PGPUB;	16:01
		and 'p-type electrode'	EPO; JPO;	
			DERWENT;	
_	78	@ad<=20000203 and 'substrate' with 'GaN'	IBM_TDB USPAT;	2004/05/29
-	/ *	with 'sapphire' and 'n-type electrode'	US-PGPUB;	06:07
		and 'p-type electrode'	EPO; JPO;	****
		and p offic officers	DERWENT;	
			IBM_TDB	
-	854	@ad<=20000203 and 'refractive index' with	USPAT;	2004/05/29
		'GaAs'	US-PGPUB;	06:03
			EPO; JPO; DERWENT;	
			IBM TDB	
1 -	18	@ad<=20000203 and 'GaN substrate' and	USPAT;	2004/06/01
1]	'n-type electrode' and 'p-type electrode'	US-PGPUB;	08:32
			EPO; JPO;	
	:		DERWENT;	
		0-4-20000202 1 12-31 1 12-5	IBM_TDB	2004/05/20
-	2	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'pad'	USPAT; US-PGPUB;	2004/05/29
		erectione with ban.	EPO; JPO;	07.34
			DERWENT;	
			IBM TDB	
-	1	@ad<=20000203 and 'GaN substrate' and	USPAT;	2004/05/29
		'thin' with 'n-type electrode'	US-PGPUB;	07:36
			EPO; JPO;	
			DERWENT;	
_	12	@ad<=20000203 and 'n-type electrode' and	IBM_TDB USPAT;	2004/05/29
		'p-type electrode' and 'pad electrode'	US-PGPUB;	07:37
		2	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/05/00
-	0	•	USPAT;	2004/05/29
		'ITO' with 'n-type electrode'	US-PGPUB; EPO; JPO;	08:23
			DERWENT;	
			IBM TDB	
-	0	•	USPĀT;	2004/05/29
		'n-type electrode'	US-PGPUB;	08:23
			EPO; JPO;	
			DERWENT;	
_	124	 @ad<=20000203 and 'GaN' and 'ITO' with	IBM_TDB USPAT;	2004/05/29
	124	'electrode'	US-PGPUB;	08:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	0	@ad<=20000203 and 'GaN' and 'ITO' with	USPAT;	2004/05/29
		'n' adj1 'electrode'	US-PGPUB;	08:34
			EPO; JPO;	
			DERWENT;	i
			IBM_TDB	
_	61	@ad<=20000203 and 'transparent' same	USPĀT;	2004/05/29
		'n-type electrode'	US-PGPUB;	08:45
			EPO; JPO;	
			DERWENT;	i
			IBM TDB	
_	0	<pre>@ad<=20000203 and 'n-type electrode' with</pre>	USPĀT;	2004/05/29
		'ITO'	US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20000203 and 'n-type electrode' same	USPAT;	2004/05/29
		'indium tin oxide'	US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20000203 and 'n-type electrode' same	USPAT;	2004/06/01
	_	'ITO'	US-PGPUB;	08:06
			EPO; JPO;	
			DERWENT;	!
			IBM TDB	1
_	2	"20010042860"	USPĀT;	2004/05/30
	-	20010012000	US-PGPUB;	09:21
			EPO; JPO;	03.22
	1		DERWENT;	
			IBM TDB	
_	0	JP10-163531	USPAT;	2004/05/30
	"	0110 103331	US-PGPUB;	09:22
			EPO; JPO;	03.22
			DERWENT;	
			IBM TDB	
_	2	'JP 10163531'	USPAT;	2004/05/30
_	2	0. 10103031	US-PGPUB;	09:24
	İ		EPO; JPO;	03.21
			DERWENT;	
			IBM TDB	
_	83	yamada-motokazu.in.	USPAT;	2004/05/30
_	63	yamada-mocokazu.in.	US-PGPUB;	09:25
			EPO; JPO;	09.23
			DERWENT;	
			1	
	1 34	made metakany in and ITED!	IBM_TDB	2004/05/30
_	34	yamada-motokazu.in. and 'LED'	USPAT;	09:25
			US-PGPUB;	09:25
			EPO; JPO;	
			DERWENT;	İ
	1	1	IBM TDB	I